

Sub B

1.(amended) An electrostatic discharge (ESD) protective structure that protects an integrated circuit connected between a first voltage bus with a first supply voltage (VCC) and a second voltage bus with a second supply voltage (VSS), said electrostatic discharge protective structure comprising:

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a plurality of laterally designed bipolar transistors each having a first load line connected to the first voltage bus and a second load line connected to the second voltage bus, wherein said first load lines are electrically parallel and said second load lines are electrically parallel to one another, each of said laterally designed bipolar transistors includes a control connection connected to one of the voltage buses;

a single track resistor (RB) co-integrated into a semiconductor body, wherein said single track resistor precedes every control connection (B) of said laterally designed bipolar transistors (T1-T3).

2.(amended) The electrostatic discharge protective structure of claim 1, wherein said semiconductor body has embedded therein at least one emitter zone and at least one collector zone of the first conduction type and at least one base zone of the second, opposite conduction type, wherein a well-shaped region is inserted into said semiconductor body between said zones of the first conduction type and said base zone or said base zones, so as to extend the effective mean free path of the charge carriers to said base zone.

6.(amended) The electrostatic discharge protective structure of claim 5, wherein said base
A³ zones laterally enclose said emitter zones and said collector zones.